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BINP SB RAS

Vacuum and cryogenic design of the CW-final focus

A. Krasnov

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USTC, China, Hefei



- Input conditions and parameters
- General assembly with detector
- Design and common assembly of IP, Y chambers and cryostat
- SR flux and power distribution
- Electron clouds
- Resistive wall loses.
- Temperature of vacuum chambers inside superconducting quadrupoles
- Conclusion

Input conditions and parameters

We are going to develop an universal design and technologies for FF elements, which can be used not at test facility in VAPP4 tunnel only but also at SCTF. It means we have to take into account proposed SCTF beam and SR parameters at highest energy:

E [GeV]	3.5		
I(A)	2.9		
Perimeter [m]	936		
$N_{e/bunch} \times 10^{-10}$	5.8		
N _b /q	974/1093		
σ_s (mm) (SR/IBS+WG)	8/14		
SR power [W/mrad]	84		
SR flux [Ph/mrad]	1,3E18		
Distance from IP to SR source [m]	16.3		

General requirements

- 1. The average residual gases pressure : $< 3 \times 10^{-7} \times$ Perimeter/FF_length x $0.4 \approx 3 \times 10^{-5}$ Pa (lower is better)
- 2. SR should not irradiate IP chamber (detector background)
- 3. All elements, with the exception of beryllium IP chamber, must be placed inside 10 degree cone with an apex at IP
- 4. To avoid RF cavity at IP (high mode capture), the diameter of vacuum chambers (in one direction at least) shall not be less that diameter of IP chamber
- 5. To minimize geometrical impedance, the vacuum chambers must be as smooth as possible (with smooth transitions between elements with deferent cross-section) ³



We are going to install the both pre-assembled cryostat with IP chambers into detector from one side.

In principle, the assembly from both sides (Super KEKB variant) with the use remote control vacuum flange is also possible



BINP Remote control flange prototype



Parts of the flange connection

Assembled connection

- We've got successful result with Cu and Al gaskets at pressure 150 atmosphere. Leak rate is less than 1E-10 mbar*L/s.
- Note, the connection keeps smoothness of internal surface along beam propagation













Vacuum chamber inside cryogenic magnets. Super KEKB case





Resistive wall loses

При комнатной температуре с учетом нормального скин-эффекта:

At high frequencies or at low temperatures, when the depth of field penetration becomes less than the mean free path of electrons, the theory of anomalous skin effect is used, which takes into account the scattering of electrons at the interface (surface). A more strict criterion for the region of the anomalous skin effect is written as follows:

Borderline frequency between normal and anomalous skin effect:

One of the best approach for surface impedance, which works well for wide frequency region is:

$$R_{s}(\omega) = \left(\frac{\sqrt{3}}{16\pi} \cdot \frac{l}{\sigma_{c}}\right)^{1/3} Z_{0}^{2/3} \frac{\omega^{2/3}}{c^{2/3}} (1 + 1.157\alpha^{-0.276}) = B \frac{\omega^{2/3}}{c^{2/3}} (1 + 1.157\alpha^{-0.276})$$

Integration over beam frequency spectra for a circular beam pipe gives:

$$P_{\rm AC3} = \frac{1}{\pi} \cdot \frac{q_e N_b I}{2\pi b} \int_0^\infty R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_c}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{5}{6}\right) + 1.157 \cdot \left[\frac{3}{4} \cdot \frac{Z_0}{\sigma_s} \left(\frac{l}{\sigma_s}\right)^2 \sigma_c^3\right]^{-0.276} \Gamma(0.7)} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\frac{L}{\sigma_s}\right)}{4\pi^2 b \sigma_s^{5/3}} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\Gamma\left(\frac{L}{\sigma_s}\right) + 1.157 \cdot \left(\frac{L}{\sigma_s}\right)}{\pi^2 c^2} \sigma_s^2\right)} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\frac{L}{\sigma_s}\right)}{\pi^2 c^2} \sigma_s^2} q_e N_e R_s(\omega) e^{-\sigma_s^2 \frac{\omega^2}{c^2}} \partial \omega = \frac{B \cdot c \cdot \left(\frac{L}{\sigma_s}\right)}{\pi^2 c^2} \sigma_s^2} q_e N_e R_s(\omega)$$

It makes good approach for Cu at temperature from LHe up to 60-80K and beam rms length up to 2 cm 1

$$P_{\rm NSE} = \frac{\Gamma\left(\frac{3}{4}\right)c}{4\pi^2 b\sigma_s^{3/2}} \sqrt{\frac{Z_0}{2\sigma_c}} \cdot q_e N_e I$$

$$\alpha = \frac{2}{3} \left(\frac{l}{\delta} \right)^2 = \frac{3}{4} \cdot \frac{\omega Z_0}{c} \left(\frac{l}{\sigma_c} \right)^2 \sigma_c^3 > 1$$

$$f_t = \frac{2}{3\pi} \cdot \frac{c}{Z_0} \left(\frac{l}{\sigma_c}\right)^{-2} \sigma_c^{-3}$$



 E_s – average energy of secondary electrons (about 2 eV)

For SCTF parameters the saturations density of electron cloud is $5e6 \ 1/cm^3$ in the chamber with ID 30mm.

Taking into account average energy of the electrons 200 eV after bunch propagation and bunch spacing 1m, one can obtain heat load due to EC **40 W/m** It looks like the mitigation of the EC with the use a coating (amorphous carbon for example) is necessary. Otherwise, the vacuum chamber operation inside quads is

possible at RT only.

Electron cloud formation at δ_{\max} <1

Phenomenologically, neglecting space charge, electron density can be estimated as:

$$\boldsymbol{\rho}_{e} = \frac{Y \cdot g \cdot \dot{\gamma} \cdot \tau_{b}}{\pi r^{2} (1 - \delta_{eff})} < 5\text{E5 cm}^{-3}$$

- The problem is solved if s <0,1 and δ_{max} < 0,9 One can obtain: $\rho_e \approx 4\text{E5 cm}^{-3}$

And heat load ~ 3 W/m

How to reach it:

- amorphous carbon coating
- High quality NEG (TiZrV)
- Laser treatment
- Or just Ti but deposited in-situ (!)

Geometrical solutions with low "g"?

$$\delta_{eff} = \int_{0}^{\infty} \delta(E_e) n_e(E_e) dE_e$$



SEY of OFE Copper

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Heat load. Cu chambers inside Q at 60 – 70 K

IP and Ychambers Total power (paraffinic coolant)

Material		b [mm]	Length [MM]	σ _c [1/(Ом·м)]	P (RW) [W]	Total P (RW) [W]	P (SR)	Тс 15
Be Ti	IP	7.5 7.5	114 140	2.5E7 2E6	14 59	73	0	01
Au (coating)		7.5	254	4.35E7		23	0	1(
Cu	γ	5	190	5.7E7	23	20	27	Ca
Cu	· ·	7,5	190	5.7E7	15	38	57	CC

Total power 150W or 100W in case Au coating

For Cu chambers at 60-80K (for one cryostat)

element	b [m]	Lengt h [mm]	σ _c [1/(Ом·м)]	P (RW) [W}	P (SR) [W]	P(EC) [W] s=0.1, σ _{eff} =0.9	P total [W]
Q0	0.015	620	5,7E8	8	3.5	2	13.5
Q1	0.024	620	5,7E8	5	6	2	13
transition	0,015 – 0,024	-	-	-	47	~4	51

Total heat load on cryogenic level 60 – 80K is 27W if transition between Q0 and Q operates at RT

Conclusion

- The first iteration of the FF elements layout has been completed
- Estimations of resistive, SR and EC heat loads have been carried out
- Operation at 60 80K of the chambers inside quads looks possible for SCTF
- All manufacturing technologies and assembly concepts can be tested at the VEPP-4CW stand.
- To simulate heat losses, it is necessary to build in resistive heating of vacuum chambers for the VEPP-4CW stand
- To make a decision on the temperature regime of the vacuum chambers inside quads, it is necessary to carry out numerical modeling of electron clouds and calculate the pressure of residual gases taking into account the SR and EC



Thanks for your attention!